



DMN1008UFDFQ

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
401/	8mΩ @ V _{GS} = 4.5V	12.2A
12V	12.5mΩ @ V _{GS} = 2.5V	10.4A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- **Battery Management Application**
- **Power Management Functions**
- **DC-DC Converters**

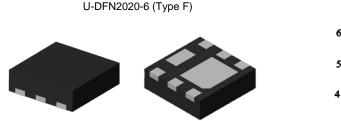
12V N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- 0.6mm Profile Ideal for Low Profile Applications .
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN1008UFDFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities. https://www.diodes.com/quality/product-definitions/

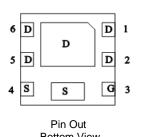
Mechanical Data

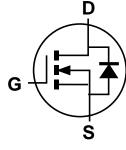
- Case: U-DFN2020-6 •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.0065 grams (Approximate)



Top View

Bottom View





Bottom View

Internal Schematic

Ordering Information (Note 4)

Part Number	Reel Size (inches)	Case	Quantity per Reel
DMN1008UFDFQ-7	7	U-DFN2020-6 (Type F)	3,000
DMN1008UFDFQ-13	13	U-DFN2020-6 (Type F)	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



8N = Product Type Marking Code

YWX = Date Code Marking

Y = Year (ex: 0 = 2020)W = Week (ex: a = Week 27; z Represents Week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Key												
Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	9	0	1	2	3	4	5	6	7	8	9	0
Week	1-26			27-52			53					
Code	A-Z			A-Z a-z			Z					
Internal Code	Su	un	Mor	ı	Tue		Ned	Thu	1	Fri		Sat
Code	7	Г	U		V		W	Х		Y		Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		Vdss	12	V	
Gate-Source Voltage		V _{GSS}	±8	V	
Continuous Drain Current, V _{GS} = 4.5V (Note 6)	Steady State	T _A = +25°C T _A = +70°C	lo	12.2 9.8	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	6)		Ідм	60	A
Continuous Source-Drain Diode Current (Note 6)	T _A = +25°C	ls	1.8	A	
Avalanche Current, L = 0.1mH (Note 7)	las	16.4	A		
Avalanche Energy, L = 0.1mH (Note 7)	Eas	13.5	mJ		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	D -	0.7	W
Total Power Dissipation (Note 5)	T _A = +70°C	PD	0.4	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	168	°C/W
Total Dower Dissinction (Note 6)	T _A = +25°C	P	1.7	W
Total Power Dissipation (Note 6)	T _A = +70°C	PD	1.0	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	74	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{0JC}	12	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

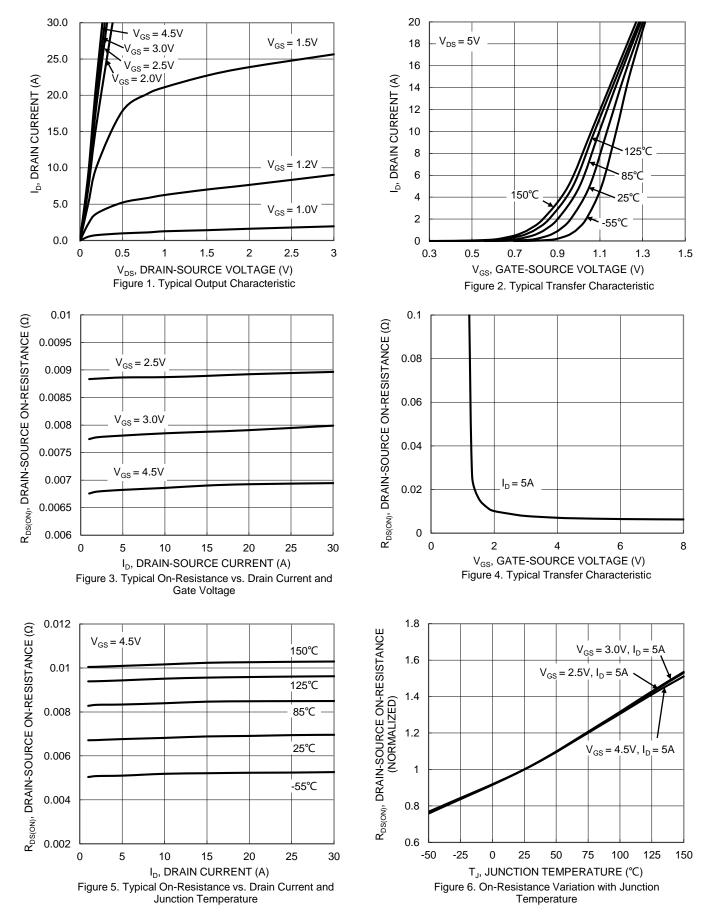
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	• • • • • •		• 76		•	
Drain-Source Breakdown Voltage	BV _{DSS}	12	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	_	—	1	μA	V _{DS} = 9.6V, V _{GS} = 0V
Gate-Source Leakage	lgss	—	—	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)				•		÷
Gate Threshold Voltage	Vgs(th)	0.3	—	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
			6.6	8		Vgs = 4.5V, ID = 5A
Static Drain-Source On-Resistance	RDS(ON)	—	7.6	11	mΩ	$V_{GS} = 3.0V, I_{D} = 5A$
			8.5	12.5		V _{GS} = 2.5V, I _D = 5A
Diode Forward Voltage	Vsd	—	0.7	1.2	V	$V_{GS} = 0V$, $I_{S} = 5A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	—	995	—		
Output Capacitance	Coss	—	305	—	pF	$V_{DS} = 6V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	—	270	—		1 = 1.00012
Gate Resistance	Rg	—	1.5	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	—	13.6	—		
Total Gate Charge (V _{GS} = 8V)	Qg	—	23.4	—	nC	
Gate-Source Charge	Qgs	—	1.3	—	nC	$V_{DS} = 6V, I_D = 5A$
Gate-Drain Charge	Q _{gd}	—	3.3	—		
Turn-On Delay Time	tD(ON)	—	3.5	—		
Turn-On Rise Time	tR	_	6.6	—		$V_{DS} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	—	17.5	—	ns	$R_G = 2\Omega, I_D = 5A$
Turn-Off Fall Time	tF	—	7.5	—		
Reverse Recovery Time	t _{RR}	_	15	—	ns	I _F = 5A, di/dt = 200A/µs
Reverse Recovery Charge	Q _{RR}	—	4	—	nC	IF = 5A, di/dt = 200A/µs

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:

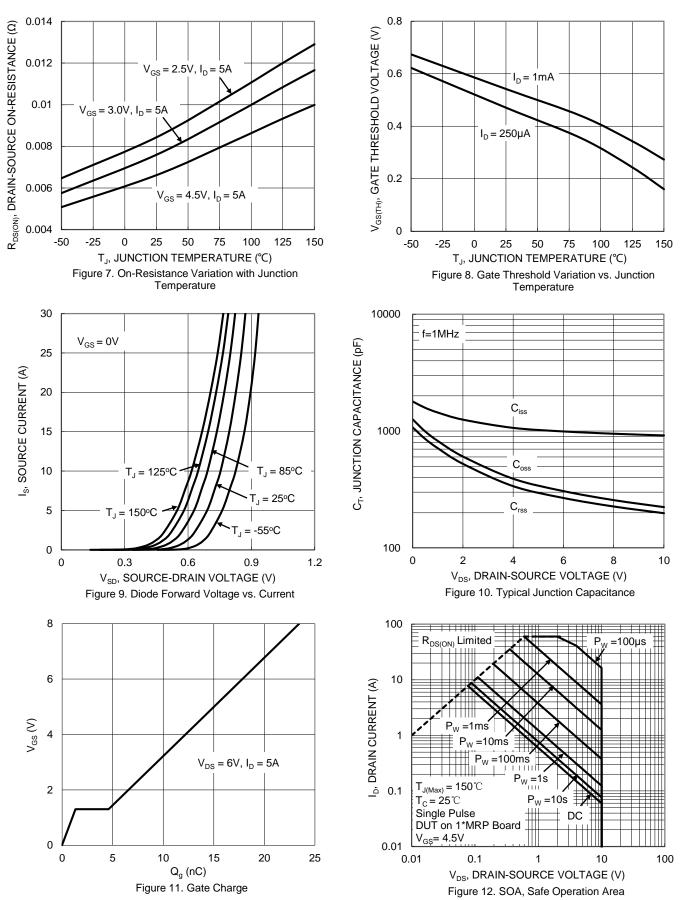


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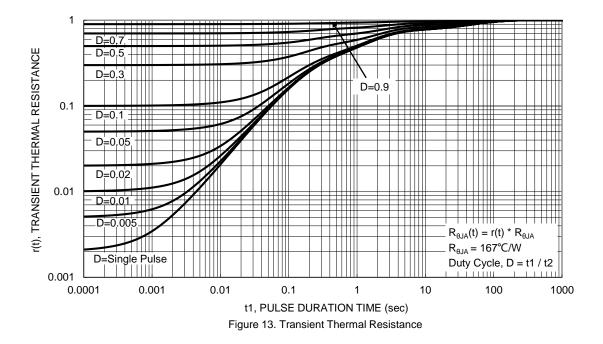
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DMN1008UFDFQ Datasheet number: DS42430 Rev. 2 - 2



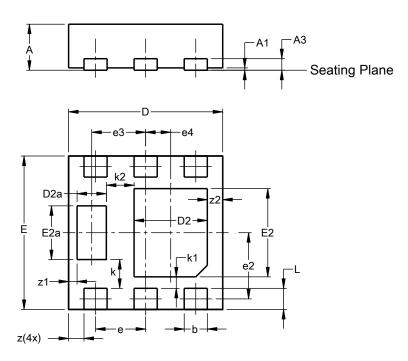






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



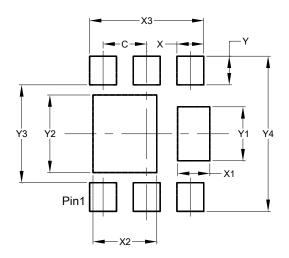
U-DFN2020-6	(Type F)
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U-DFN2020-6							
(Type F)							
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
E	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е	0.65 BSC						
e2	0.863 BSC						
e3		0.70 BS	С				
e4	C).325 BS	SC				
k		0.37 BSC					
k1	0.15 BSC						
k2	0.36 BSC						
L	0.225 0.325 0.275						
z	0.20 BSC						
z1	0.110 BSC						
z2	0.20 BSC						
All C	imens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value
Dimensions	(in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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